

Architectures for new pixel chip/cells

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FE-I4 chip for ATLAS

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FE-I4 Specs



Pixel size	50 x 250	μm²
Pixel array size	80 x 336	Col x Row
Normal pixel input capacitance range	100-500	fF
Edge pixels input capacitance range	150-700	fF
In-time threshold with 20ns gate (400 fF)	4000	е-
Single channel ENC sigma (400 fF)	<300	e-
Tuned threshold dispersion	<100	е-
Charge resolution (ToT method)	4	bits
Charge resolution (ToT method) Operating temperature range	4 -40 to +60	°C
Charge resolution (ToT method) Operating temperature range Radiation tolerance	4 -40 to +60 300	°C MRad
Charge resolution (ToT method) Operating temperature range Radiation tolerance DC leakage current tolerance	4 -40 to +60 300 100	bits °C MRad nA
Charge resolution (ToT method) Operating temperature range Radiation tolerance DC leakage current tolerance Single serial command input (nominal)	4 -40 to +60 300 100 40	bits °C MRad nA Mb/s
Charge resolution (ToT method) Operating temperature range Radiation tolerance DC leakage current tolerance Single serial command input (nominal) Single serial data output (nominal)	4 -40 to +60 300 100 40 160	bits °C MRad nA Mb/s Mb/s
Charge resolution (ToT method) Operating temperature range Radiation tolerance DC leakage current tolerance Single serial command input (nominal) Single serial data output (nominal) Output data encoding	4 -40 to +60 300 100 40 160 8b/10b	bits °C MRad nA Mb/s Mb/s

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FE-I4A at a glance



FE-I4A chip overview





FE-I4 analog



Analog Pixel

Two-stage Amplifier configuration

- Optimized for low power, low noise and fast rise time
- The second stage Amp2 is AC coupled to the preamplifier
 - Additional gain Cc/Cf2~ 6
 - decoupled from preamplifier DC potential shift caused by leakage
- The main motivation on the 2 stage structure is to provide a High gain
 - More flexibility on the choice of Cf1
 - The charge collection less dependent on the detector capacitor
- Local DACs for tuning feedback current and global threshold
- Charge injection circuitry for testing and characterization
- 13 bits for pixel configuration:
 - 4 FDAC: tuning feedback current
 - 5 TDAC: tuning of discriminator threshold
 - 2 Local charge injection circuitry
 - 1 Hit Enable
 - 1 HitBus / IleakMonitor





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FE-I4 digital



Pixel Digital Region

In the present chip (FEI3) :

- Each pixel is logically independent inside the DC
- All hit pixels are shipped to End of Column buffer
- A hit pixel need to transfer its data to EoC before accepting new hit : Congestion Problem for a high hit rate
- For the FEI4 chip
 - Basic idea is to store the hit locally until L1T
 - Implementation of local buffers is possible because of the smaller feature size (130 nm)
 - Organized on PDR : Pixel Digital Region
- A PDR processes the data from 4 pixel discriminator
 - Store locally up to 5 events/hits (different BC)
 - Small/big hit discrimination (3 programmable modes)
 - 2 BC association for small hit
 - 4 bit ToT (small hit, no hit, long hit, 13 x value)
 - Neighbor logic (1 bit)
 - Records up to 16 consecutive triggers (4 bit)
 - Programmable latency max. 257 BC
 - Token type readout



An interesting CERN development



SC_130nm_XL Library

- Row Height is fixed to 2.4 μm
- Well Tap library
- Maximum frequency <~350 MHz
- Low power transistors
- ~45 cells are available in the library (growing fast...)
 - No SEU registers (so far)
- Encounter Library Characterizer (ELC) has been used to fully characterize the library in different corners
 - Full Synopsis library
 - Verilog library
 - LEF files





- **Basic considerations:**
- •If we come to the conclusion that the best is to do like ATLAS, just use FE-I4 (maybe with some adaptation...)
- •FEI-4 designed by a large community: many different architectures considered in the preliminary simulations: not trivial to do better.
- •A complete new chip only motivated if looks reasonably different and already targets phase 2 specs.





- The front-end dead-time defines the ultimate efficiency.
- With a ToT scheme longer hits can be tolerated if they are less probable.
- 100 um x 100 um and 250 MHz (1GHz) /cm² : 25 kHz/100 kHz pixel.
- Average allowable dead-time for 0.5 % pile up probability: 200 ns (50 ns).
- I60 MHz clock=6.25 ns time bin=8 counts for the average value.
- ToT still usable up to the highest rates.
- Faster digitization techniques could also be considered (space?!)
- More than 4 bits impractica in pixel, unless one used analog sampling and out of pixel digitization.





Straightforward approach:

- Re-optimize the front-end to cope with the new ToT time: try to benefit from the shorter ToT to simplify and spare some area.
- In the present chip, significant filtering capacitance is used to have a very linear ToT also for long ToT values and high leakage current









- Maintain the same approach: the pixel is read-out when hit, regardless if the hit is validated or not.
- Transfer all the hit to the periphery, where trigger matching is done.
- Present time for a pixel to transmit data (after it has been addressed): 56.25 ns (9 clock cycles at 160 MHz). "This time is very conservative (for PANDA was more than enough), but it could be significantly reduced" (Gianni dixit!).
- Pros': straightforward extension of the present design
- Con's: transferring to the periphery hits which then are discarded is power inefficient
- More buffering is needed at the periphery, more dead area.
- We are now evaluating this solution: it is not the most efficient one, but we know it very well so it serves as a useful benchmark. Also useful to set-up the simulation environment.



- At present, the time stamp is distributed with a pseudo-differential CMOS logic to minimize injection of noise: 24 lines to distributed 12 bits
- The technology has many insulation features, so this is probably not necessary.
- Singled ended time stamp distribution: 12 lines are freed to send a trigger time stamp.
- Actually, we do not need 12 bits: 10 are sufficient (10 bit counter at 160 MHz provides a maximum dynamic range of 6.4 us, more than sufficient to accommodate the trigger latency of 3.2 us).



Trigger matching on pixel?





Trigger matching on pixel?



When the pixel fires the value of the running time stamp bus is stored into the leading edge register. The leading edge register keeps data for some time: SEU protected

When the trailing edge arrives, the time stamp is stored into a temporary register: the ToT is calculated and stored into the ToT register. The temporary register is one per pixel and does not need triplication (short storage time). Alternative: use a counter for ToT measurement (requires distribution of clock).

When a trigger arrives the trigger time stamp is calculated accounting for the latency an issue on the trigger bus (à la SuperB layer0).

The buffers compare the stored values with the trigger time stamp and if a match is found the pixel is selected for read-out.

The buffer compare also the stored value with the current time stamp and when the two matches the buffer is cleared (or after a read-out).

"Four buffers needed to accommodate 3.2 us latency with negligible event loss "(Lino (and Poisson) dixerunt)





- Presently the leading edge register is 12 bits and is 10 um x 100 um with triplication
- The trailing edge register is equal to the leading edge
- In case of multi-buffering and short ToT storing both leading and trailing edges and calculating the ToT off-line in area inefficient.
- A 14 bits register to store both leading edge and ToT would take 12 um x 100 um (?).
- Four buffers would take 50 um x 100 um
- Then one must add the control logic and the triggering/time-out logic
- The configuration register in the present version is 14.4 um x 84 um
- However the new CERN cells allow a typical 2x saving in area compared with the standard cell used for the present ToPiX version
- Radiation policy?
- In ToPiX triple redundance and majority voting everywhere
- FE-I4: simple DICE cells for data storage, DICE cells AND triple redundancy for control registers. Ok for phase 1. What for phase 2?
- A pixel with local trigger matching and independent pixel not a priori impossible, but of course must be checked in reality.





- Perform a detailed study of the "straightforward adapation" (i.e. "read all hit pixels, read faster, match trigger in the EoC"). Simulations already started by Giulio Dellacasa.
- Study of the in-pixel logic for the local trigger matching to confirm is this is realistic.
- Define a clear prototyping strategy for the future.
- In pixel chips too small prototypes are useless unless one is trying really something fancy (i.e. 45 nm?)
- What is useful: prototype of reasonable size (à la ToPiX 3), bump bondable to a sensor.
- Complex building blocks which are not indispensable on the first prototype, but are of course fundamental in the final one (e.g PLL for clock multiplication, robust biasing generators, etc...).
- Also a more elaborate version of the EoC logic may come later (e.g. the EoC logic of ToPiX_v2 was minimal to allow to read-out the chip)